

Shuji Nakamura, Ph.D., Professor of Materials Department, University of California Santa Barbara

Education

University of Tokushima, Japan, Doctor of Engineering, 1994

University of Tokushima, Japan, Master of Electronic Engineering, 1979

University of Tokushima, Japan, Bachelor of Electronic Engineering, 1977

Academic Appointments

1999-Present University of California Santa Barbara, Professor, Materials Department

1993-1999 Nichia Chemical Ind., Ltd., Senior Researcher, Department of Research and Development (R&D)

1989-1993 Nichia Chemical Ind., Ltd., Group Head, Research and Development 2nd Section

1988-1989 University of Florida, Visiting Research Associate, Electronic Engineering

1985-1988 Nichia Chemical Ind., Ltd., Group Head, Research and Development 1st Section

1979-1984 Nichia Chemical Ind., Ltd., Research and Development

Examples of Honors & Awards

1994, 1997 Best Paper Award of Japanese Applied Physics Society

1998 British Rank Prize

2000 Honda Award

2002 Takeda Award

2002 The Economist Innovation Award “No Boundaries”

2006 Millennium Technology Prize

Summary of Inventions

1990 Develops new “two flow” MOCVD equipment

1992 Discovers p-type GaN using thermal annealing process, discovers Hydrogen passivation of p-type GaN

1992 Successfully grows InGaN single crystal layers

1993 Demonstrates 1 mW InGaN DH blue LED

1995 Demonstrates 5 mW InGaN QW blue and green LEDs

1995 Announces first pulsed blue InGaN based injection laser

1996 Announces first CW blue InGaN based injection laser